MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK155U60Z1

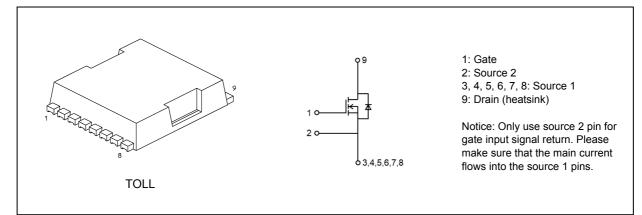
1. Applications

• Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.13 \Omega$ (typ.)
- (2) High-speed switching properties with the lower capacitance.
- (3) Enhancement mode: $V_{th} = 3$ to $4 V (V_{DS} = 10 V, I_D = 0.61 mA)$

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25$ °C unless otherwise specified)

Characteristics			Rating	Unit
Drain-source voltage		V _{DSS}	600	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	I _D	17	A
Drain current (pulsed)	(Note 1)	I _{DP}	68	7
Power dissipation (T _c = 25	°C)	PD	130	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	163	mJ
Single-pulse avalanche current		I _{AS}	3.8	A
Reverse drain current (DC)	(Note 1)	I _{DR}	17	7
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	68	7
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150]

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance		0.961	°C/W

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_DD = 90 V, T_ch = 25 °C (initial), L = 20 mH, I_{AS} = 3.8 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V_{DS} = 600 V, V_{GS} = 0 V	_		2	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.61 mA	3	_	4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 5.4 A		0.13	0.155	Ω

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance		C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	1350	—	pF
Reverse transfer capacitance		C _{rss}		—	1.7	—	
Output capacitance		C _{oss}		_	35	—	
Effective output capacitance (energy related)	(Note 3)	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V	_	60	_	
Effective output capacitance (time related)	(Note 4)	C _{o(tr)}		_	410	_	
Gate resistance		r _g	V _{DS} = OPEN , f = 1 MHz	_	3.4	_	Ω
Switching time (rise time)		t _r	See Figure 6.2.1	_	15	_	ns
Switching time (turn-on time)		t _{on}		_	34	—	
Switching time (fall time)		t _f		_	5	_	
Switching time (turn-off time)		t _{off}]	_	70	_	
MOSFET dv/dt ruggedness		dv/dt	$V_{DS} \leq V_{DSS}, \ I_D \leq 8.5 \ A$	70		_	V/ns

Note 3: $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0V to 400V. Note 4: $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0V to 400V.

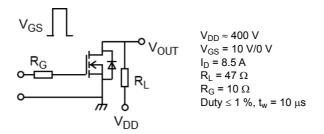


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400$ V, V_{GS} = 10 V, I_D = 17 A	_	24	—	nC
Gate-source charge 1	Q _{gs1}		_	7.7	_	
Gate-drain charge	Q _{gd}			7	_	

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 17 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	V _{DD} = 400 V,	_	270	_	ns
Reverse recovery charge	Q _{rr}	I _{DR} = 8.5 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs	_	2.7	_	μC
Peak reverse recovery current	I _{rr}	$-di_{DR}/dt = 100 A/\mu s$	_	20		А
Diode dv/dt ruggedness	dv/dt	$V_{DD} \leq 400$ V, $I_{DR} \leq 8.5$ A, V_{GS} = 0 V	40	_	_	V/ns

7. Marking (Note)

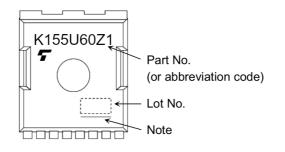


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

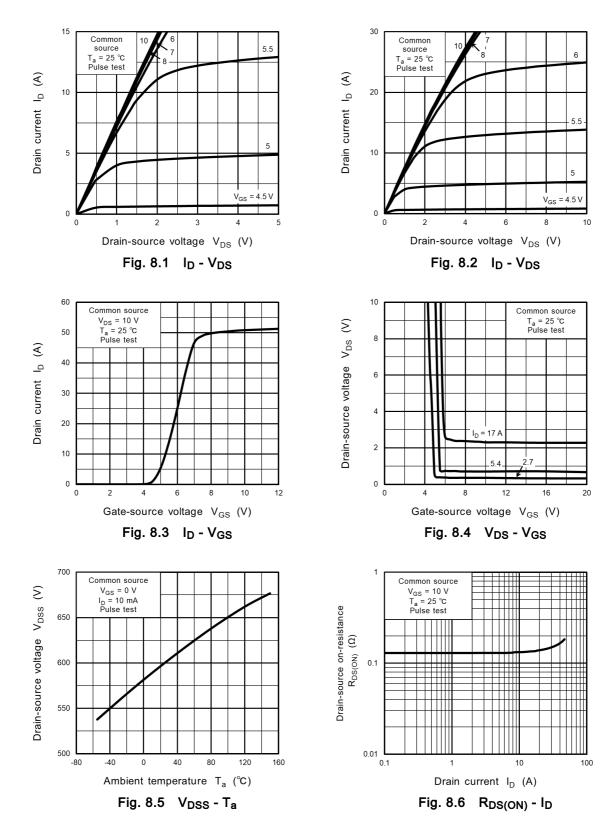
Not underlined: [[Pb]]/INCLUDES > MCV

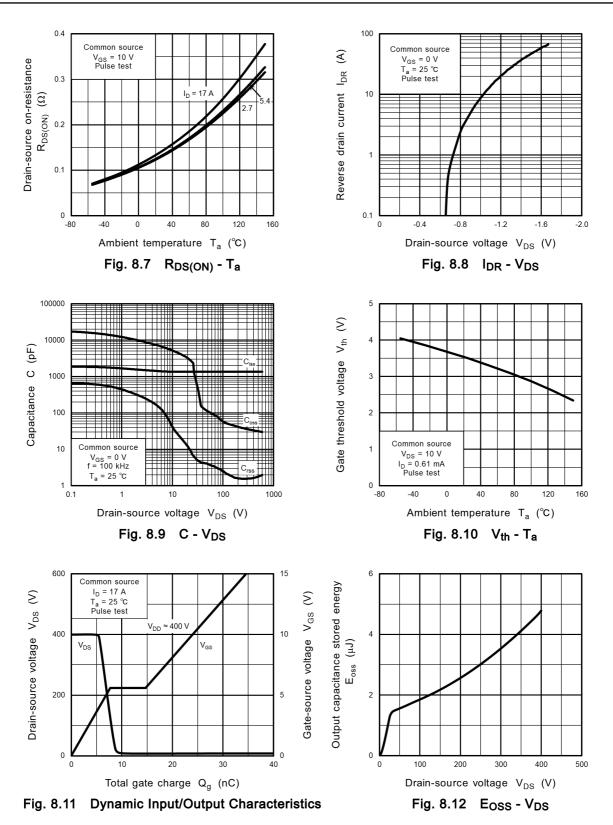
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

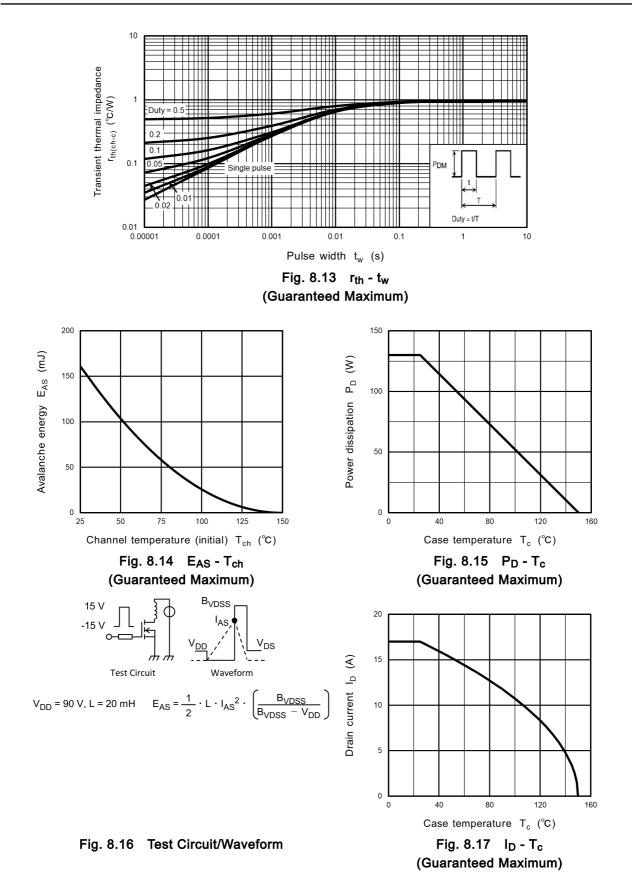
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

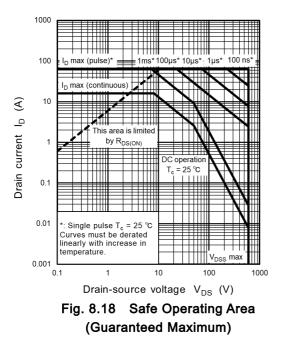
The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)







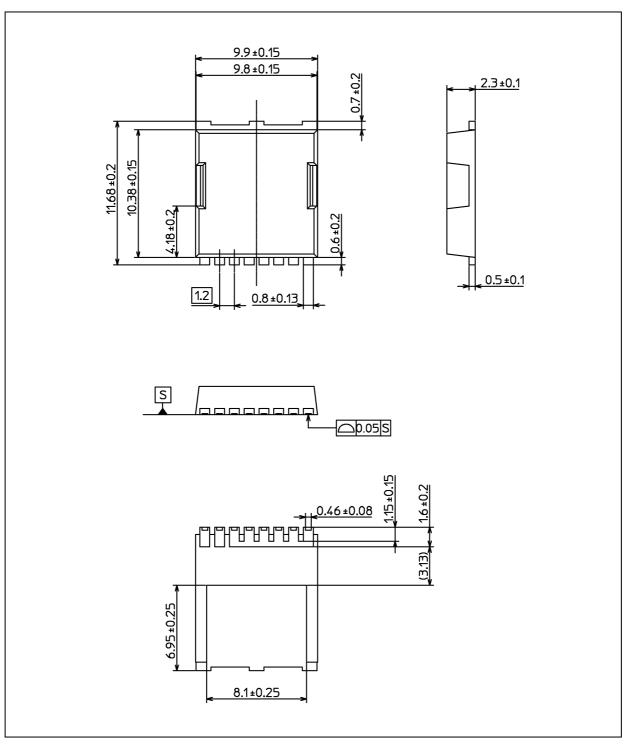


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.75 g (typ.)

Package Name(s)	
TOSHIBA: 2-10AF1A	
Nickname: TOLL	

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